

ABSTRACT

5 PROCESS FOR THE FABRICATING AN ELECTRONIC INTEGRATED CIRCUIT AND ELECTRONIC INTEGRATED CIRCUIT THUS OBTAINED

10 A process for fabricating an electronic
integrated circuit comprises the formation on a
substrate (100), of which a part is composed of
absorbing material, of a portion (1) made of a
sacrificial material. The sacrificial material includes
cobalt, nickel, titanium, tantalum, tungsten,
15 molybdenum, gallium, indium, silver, gold, iron and/or
chromium. A rigid portion (3,4) is formed in fixed
contact with the substrate, on one side of the portion
of sacrificial material (1) opposite to the part of the
substrate composed of absorbing material. The circuit
20 is heated such that the sacrificial material is
absorbed into the part of the substrate composed of
absorbing material. A substantially empty volume (V) is
thus created in place of the portion of sacrificial
material (1). Said volume that is substantially empty
25 can replace a dielectric material situated between the
electrodes of a capacitor.

Figure 4